

# P Murugapandiyan

## List of Publications by Year in descending order

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Version: 2024-02-01

21  
papers

225  
citations

1162889

8  
h-index

1058333

14  
g-index

21  
all docs

21  
docs citations

21  
times ranked

165  
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanosheet field effect transistors-A next generation device to keep Moore's law alive: An intensive study. <i>Microelectronics Journal</i> , 2021, 114, 105141.	1.1	50
2	Design and analysis of 30Ånm T-gate InAlN/GaN HEMT with AlGaIn back-barrier for high power microwave applications. <i>Superlattices and Microstructures</i> , 2017, 111, 1050-1057.	1.4	31
3	DC and microwave characteristics of Lg 50 nm T-gate InAlN/AlN/GaN HEMT for future high power RF applications. <i>AEU - International Journal of Electronics and Communications</i> , 2017, 77, 163-168.	1.7	26
4	Switching Transient Analysis and Characterization of an E-Mode B-Doped GaN-Capped AlGaIn DH-HEMT with a Freewheeling Schottky Barrier Diode (SBD). <i>Journal of Electronic Materials</i> , 2020, 49, 4091-4099.	1.0	16
5	Performance analysis of HfO <sub>2</sub> /InAlN/AlN/GaN HEMT with AlN buffer layer for high power microwave applications. <i>Journal of Science: Advanced Materials and Devices</i> , 2020, 5, 192-198.	1.5	15
6	DC and microwave characteristics of 20Ånm T-gate InAlN/GaN high electron mobility transistor for high power RF applications. <i>Superlattices and Microstructures</i> , 2017, 109, 725-734.	1.4	11
7	Investigation of Quaternary Barrier InAlGaIn/GaN/AlGaIn Double-Heterojunction High-Electron-Mobility Transistors (HEMTs) for High-Speed and High-Power Applications. <i>Journal of Electronic Materials</i> , 2020, 49, 524-529.	1.0	9
8	Breakdown voltage enhancement of gate field plate Al <sub>0.295</sub> Ga <sub>0.705</sub> N/GaN HEMTs. <i>International Journal of Electronics</i> , 2020, , 1-15.	0.9	9
9	Static and dynamic characteristics of L g 50Ånm InAlN/AlN/GaN HEMT with AlGaIn back-barrier for high power millimeter wave applications. <i>Journal of Science: Advanced Materials and Devices</i> , 2017, 2, 515-522.	1.5	8
10	Investigation of Influence of SiN and SiO <sub>2</sub> Passivation in Gate Field Plate Double Heterojunction Al <sub>0.3</sub> Ga <sub>0.7</sub> N/GaN/Al <sub>0.04</sub> Ga <sub>0.96</sub> N High Electron Mobility Transistors. <i>Silicon</i> , 0, , 1.	1.8	8
11	Influence of AlN passivation on thermal performance of AlGaIn/GaN high-electron mobility transistors on sapphire substrate: A simulation study. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021, 273, 115449.	1.7	7
12	30 nm T-gate enhancement-mode InAlN/AlN/GaN HEMT on SiC substrates for future high power RF applications. <i>Journal of Semiconductors</i> , 2017, 38, 084001.	2.0	6
13	Design and development of cross dipole antenna for satellite applications. <i>Frequenz</i> , 2020, 74, 229-237.	0.6	6
14	UWBG AlN/Î <sup>2</sup> -Ga <sub>2</sub> O <sub>3</sub> HEMT on Silicon Carbide Substrate for Low Loss Portable Power Converters and RF Applications. <i>Silicon</i> , 2022, 14, 11079-11087.	1.8	5
15	Influence of High-k Passivation Layer on Gate Field Plate AlGaIn/GaN/AlGaIn Double Heterojunction HEMT. <i>Silicon</i> , 2022, 14, 10437-10445.	1.8	5
16	GaN-Based High-Electron Mobility Transistors for High-Power and High-Frequency Application: A Review. <i>Lecture Notes in Networks and Systems</i> , 2020, , 339-348.	0.5	4
17	Investigation of ultra-scaled AlN/GaN/InGaIn double heterojunction HEMT for high-frequency applications. <i>International Journal of Electronics Letters</i> , 2020, 8, 472-482.	0.7	3
18	60 GHz Double Deck T-Gate AlN/GaN/AlGaIn HEMT for V-Band Satellites. <i>Silicon</i> , 2022, 14, 5941-5949.	1.8	3

#	ARTICLE	IF	CITATIONS
19	A 28-GHz Low-Loss AlGaIn/GaN HEMT for TX/RX Switches in 5G Base Stations. Journal of Electronic Materials, 2022, 51, 1215-1225.	1.0	3
20	High-Performance $\text{In}_{0.13}\text{Al}_{0.83}\text{Ga}_{0.04}\text{N} / \text{AlN} / \text{GaN} / \text{In}_{0.04}\text{Ga}_{0.96}\text{N}$ HEMT for High Power Millimeter Wave Electronics. , 2021, , .		0
21	DC and Microwave Characteristics of $20\text{ nm T-Gate Enhancement Mode Al}_{0.5}\text{Ga}_{0.5}\text{N/AlN/GaN/Al}_{0.08}\text{Ga}_{0.92}\text{N}$ High Electron Mobility Transistor for Next Generation High Power Millimeter Wave Applications. Journal of Nanoelectronics and Optoelectronics, 2018, 13, 183-189.	0.1	0